

MRA0610-3

Silicon NPN high power UHF transistor MRA0610-3 is designed for class C common base wideband amplifier applications in the transmitters or radio relay systems.

Output power: 5 watt
Frequency range: 350-700 MHz
Voltage: 28 volt
Package type: FO 57C (Module 2 lead)
Input Matched
Common emitter configuration
Emitter Ballasting
Aluminum Metalization

ELECTRICAL CHARACTERISTICS ($T_{CASE} = 40^{\circ} C$)

SYMBOL	TEST CONDITIONS	VALUE			UNIT
		MIN.	TYP.	MAX.	
P_{OUT}	$f_o = 700 \text{ MHz} / V_{cc} = 28 \text{ V} / P_{IN} = 0.625 \text{ W}$	5			W
G_p	$f_o = 700 \text{ MHz} / V_{cc} = 28 \text{ V} / P_{OUT} = 5 \text{ W}$	9			dB
λ_c	$f_o = 700 \text{ MHz} / V_{cc} = 28 \text{ V} / P_{OUT} = 5 \text{ W}$	40	45		%

ABSOLUTE MAXIMUM RATINGS ($T_{CASE} = 25^{\circ} C$)

Symbol	PARAMETERS	VALUE	UNIT
V_{CBO}	Collector - Base Voltage	50	V
V_{EBO}	Emitter - Base Voltage	4	V
I_C	Continuous Collector Current	1.5	A
P_C	Collector Power Dissipation	10*	W
T_j	Junction Temperature	175	$^{\circ}C$
$R_{th(j-c)}$	Junction-Case Thermal Resistance	8.2	$^{\circ}C/W$

* For Dynamic Operation, $T_{CASE} = 90^{\circ} C$